# Fluxon-sem i uxon interaction in an annular long Josephson 0--junction

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W e investigate theoretically the interaction between integer and half-integer Josephson vortices (uxons and semiuxons) in an annular Josephson junction. Semiuxons usually appear at the 0-boundary where there is a -discontinuity of the Josephson phase. We study the simplest, but the most interesting case of one -discontinuity in a bop, which can be created only articially. We show that measuring the current-voltage characteristic after injection of an integer uxon, one can determ ine the polarity of a semi uxon. Depending on the relative polarity of uxon and semi uxon the static con guration may be stable or unstable, but in the dynamic state both con gurations are stable. We also calculate the depinning current of N uxons pinned by an arbitrary fractional vortex.

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### I. IN TRODUCTION

For conventional Josephson junctions the st Josephson relation reads  $I_{\rm s}$  =  $I_{\rm c}\sin($ ), where  $I_{\rm s}$  is the supercurrent through the junction,  $I_{\rm c}$  is the critical current and is the so-called Josephson phase which is equal to the di erence of the phases of the quantum – mechanicalm acroscopic wave functions in the electrodes. The Josephson relation for a Josephson –junction is  $I_{\rm s}$  =  $I_{\rm c}\sin($ ) =  $I_{\rm c}\sin($  + ), i.e., a –junction can be considered as a junction with negative critical current or having an additional phase shift of between the phases of the wave functions (therefore the nam e). A coordingly, conventional Josephson junctions are sometimes called 0-junctions.

If one considers a 1D long Josephson 0--junction (LJJ) made of alternating parts with positive and negative critical currents (0 and -parts), half-integer ux quanta (sem i uxons<sup>1,2</sup>) may spontaneously form at the boundaries between 0 and regions.

Sem i uxons are very interesting objects which are not yet studied in detail, rst of all because up to now it was rather di cult to fabricate 0- -junctions. Recently several groups succeeded to demonstrate 0- -junctions based on various technologies: YBa<sub>2</sub>Cu<sub>3</sub>O<sub>7</sub>-Nb ramp zigzags<sup>3,4</sup>, grain boundary junctions based on tri- and tetra-crystals<sup>5,6</sup> and Nb junctions based on an arti cially created discontinuity<sup>7</sup>. Both 0 and junctions from the Superconductor-Ferror agnet-Superconductor fam ily were demonstrated by several groups<sup>8,9,10</sup> but a 0- -LJJ was not reported yet. Sem i uxons were observed using SQUID microscopy in di erent types of 0- -LJJ<sup>6,11,12,13</sup>.

A single semi uxon, formed in a LJJ of length L  $_{\rm J}$  with one 0- -boundary, is pinned at this 0- - boundary<sup>14,15</sup> and can have positive or negative polarity carrying the ux +  $_0$ =2 or  $_0$ =2, respectively. The bias

current from 0 up to  ${}^2 I_c$  ( $I_c = j_c w L$  is the \intrinsic" critical current, w is the junction width) cannot move the sem i uxon but just changes its shape<sup>14</sup>. This property suggests to use sem i uxons in information storage devices, classical or quantum.

In the classical regime the polarity of a semi uxon (positive or negative) willencode a logical 0 or 1. The inform ation encoding using semi uxons is somewhat more robust than using uxons because semi uxons cannot \escape" as they are pinned at the discontinuity point. The switching between these states can be done by injecting a single ux quantum of proper polarity into the junction.

In the quantum lim it a sem i uxon having two possible polarities is sim ilar to a spin with two possible orientations (up or down). Therefore we often use spin notation to denote the polarity of the sem i uxon, i.e., " or #. A nalogously, we denote the polarity of a uxon as \* or +. It seems that a sem i uxon is an interesting candidate to realize a qubit. It still remains a challenging task to

nd out whether the sem i uxon may stay in the superposition of both states and perform quantum tunneling between them or not. In comparison with a uxon based qubit the one based on a sem i uxon should be more robust as both " and # states represent the ground state of the system, while the uxon of any polarity is an excited state, the ground state being the one with constant phase.

For both quantum and classical bits one needs a way to determ ine the nal state of the sem i uxon, i.e., read out its polarity. Im agine the sim plest situation: a single sem i uxon of unknown polarity in an annular  $LJJ^{27}$ . Let us inject a uxon of a certain polarity into this Josephson ring som ewhere far from the sem i uxon position, e.g., using a pair of current in jectors<sup>16</sup>. If the polarities of the

uxon and of the semi uxon are di erent, the \annihilation" between uxon and semi uxon will result in a pinned sem i uxon of the opposite polarity (we assume that the bias current is zero during uxon injection). The I{V characteristic (IVC) of the resulting state has a rather largem aximum supercurrent (depinning current of a sem i uxon)  $_{c}^{"} = 2 =$  in normalized units ( = I=I<sub>c</sub>). On the other hand, if the uxon and the sem i uxon are of the same polarity, no \annihilation" takes place. If the bias current is applied, the uxon starts moving passing through the sem i uxon resulting in a nite voltage across the LJJ and rather low  $_{c}$ . In this case the depinning current  $_{c}^{*"}$  is determined by the repulsion force between

uxon and semi uxon. The uxon should overcome this pinning by the semi uxon to start moving around the ring.

In this paper we propose a technique to test the polarity of sem i uxons by introducing test uxons into the Josephson ring. M easuring the current voltage characteristic we can determ ine the polarity of sem i uxon (s) before the uxon was introduced. We also study resulting states which have di erent critical (depinning) currents and di erent dynam ics.

In section II we introduce the model which is used for numerical simulations. The numerical results are presented and discussed in section III. Section IV concludes this work.

### II. THE MODEL

The dynam ics of the Josephson phase in a LJJ consisting of alternating 0 and parts can be described by the 1D perturbed sine-G ordon equation<sup>1</sup>

$$xx \quad tt \quad sin = t \quad xx(x); \quad (1)$$

where (x;t) is the Josephson phase and subscripts x and t denote the derivatives with respect to coordinate x and time t. In Eq. (1) the spatial coordinate is normalized to the Josephson penetration depth  $_{\rm J}$  and the time is normalized to the inverse plasma frequency  $!_{\rm p}^{-1}$ ;  $= 1 = \frac{p_{\rm c}}{c}$  is the dimensionless damping ( $_{\rm c}$  is the M cC umber-Stewart parameter);  $= j=j_{\rm L}$  is the externalbias current density normalized to the critical current density of the junction. The function (x) is a step function which is -discontinuous at all points where 0 and parts join and is a constant equal to n within each part (n is an integer). For example, (x) can be equal to zero along all 0-parts and along all -parts.

It is clear from Eq. (1) that (x) is also -discontinuous at the same points as (x). Therefore, we often call the points where 0 and parts join phase discontinuity points.

N ote that to describe 0- -LJJs other authors<sup>2,17,18</sup> often use directly the equation with alternating critical current density written for the continuous phase (x;t)

$$xx \quad tt \quad sin = t \quad (x): \qquad (2)$$

The Eqs. (1) and (2) are, actually, equivalent and one

can be obtained from the other by substitution  $(x;t) = (x;t) + (x)^{1}$ .

In case of an annular LJJ one should use periodic boundary conditions (b.c.) to solve Eq. (1) or (2). In the case of a conventional annular LJJ without phase discontinuities the boundary conditions are expressed as follows

$$(L;t) = (0;t) 2 n_{\rm F};$$
 (3)

where  $n_F$  is the number of ux quanta (Josephson vortices) trapped in the ring. Note that when there are no discontinuities , so that b.c.  $\beta$ ) holds for also.

For the case of an annular LJJ with discontinuities the boundary conditions for are still given by Eq. (3). This can be understood using the following gedanken experiment. Imagine that we start from the state without discontinuities (x) = 0. Then we slowly increase a discontinuity, e.g., by using a pair of closely located

-in jectors<sup>7</sup>, at some point  $x = x_0$  from the value 0 to some value . It is clear that the Josephson phase (x) changes somehow on the length scale  $_J$  in the vicinity of  $x_0$  to compensate (to react on) this discontinuity, e.g., by form ing a fractional vortex with the center at  $x = x_0$ . In any case the phase (x) and its derivative  $_x$  (x) are smooth and continuous functions all along the junction except for the point  $x = x_0$ . A ssum ing that the discontinuity point does not coincide with x = 0 or with x = L, we can write (0) = (L) and  $_x$  (0) =  $_x$  (L). In the presence of additional uxons trapped in the junction we get b.c. (3) even in the presence of the discontinuity points.

The b.c. for can be written, recalling that = (x)

$$(L;t) = (0;t) + n_{SF} + 2 n_F;$$
 (4)

where  $n_{\rm SF}$  is the sum of all discontinuities (sem i uxons) in the ring. Note that if

$$(\mathbf{x}) = \begin{cases} X^{N} \\ {}_{iH} (\mathbf{x} \quad \mathbf{x}_{i}); \end{cases}$$
 (5)

where  $_{\rm i}$  is the i-th discontinuity and H (x) is a H eavyside step function, the expression for  $n_{\rm SF}$  is

$$n_{\rm SF} = \sum_{i=1}^{X^{\rm N}} i; \qquad (6)$$

In this paper we will investigate the following two cases

- 1. A uxon is injected into the annular LJJ containing a negative semi uxon, i.e.,  $n_F = +1$ ,  $n_{SF} = 1$ .
- 2.A uxon is injected into the annular LJJ containing a positive sem i uxon, i.e.,  $r_F = +1$ ,  $n_{SF} = +1$ .

The simulations were performed using StkJJ software<sup>19</sup> and were con med by an independently written program <sup>28</sup>.

We use = 0:1 for all results reported here. This value is not very high, so that it allows to observe some dynam ics. On the other hand, it is not very low as the majority of 0- -junctions has rather high damping. In the case & 1 the static results related to the reading out the state of a sem i uxon hold, but no dynam ical e ects such as uxon steps can be observed.

In order to visualize and to understand the uxon and sem i uxon dynamics we plot their trajectories on the (x;t) plane. U sually, to track the trajectory of a uxon one tracks the trajectory of its center. Since at a given instant of time the phase (x), corresponding to the uxon solution, changes from 0 at x ! 1 to 2 at x ! + 1, it is assumed that the center of a uxon coincides with the point where the phase = . Since the phase is de-

ned modulo 2 , in the general case the center of uxons is situated at points where = +2 k with integer k. To distinguish between uxons and anti uxons, we also check the sign of the phase derivative  $_{\rm x}$  (m agnetic eld) at the point where = +2 k. If the sign is positive, then it is a uxon and we plot its position as a black point on x{t plane. If  $_{\rm x} < 0$ , then we plot it as a gray points on the x{t plane.

W hen we deal with semi uxons, the idea is the same, but since the phase of a semi uxon changes from 0 to (mod) we have to de ne the centers of semi uxons as the points where  $= \frac{1}{2} + k$ . The sign of x at the points where  $= \frac{1}{2} + k$  is used to distinguish between semi uxons of positive and negative polarity. W ith this de nition, every 2 - uxon carrying the integer ux<sub>0</sub> results in two points on the x{t plane, i.e., its trajectory will be represented by a double line.

Below we present num erical results obtained for an annular junction of length L = 8  $_{\rm J}$ .

#### A. One sem i uxon in a ring

F irst we investigate num erically an annular LJJ with only one phase discontinuity point.

Here and below, without loosing generality, we assume that the injected uxons have positive polarity \*  $[P_{\rm F} = +1 \text{ in } (4)].$ 

### 1. Negative sem i uxon

If initially the semi uxon has negative polarity # [n<sub>SF</sub> = 1 in (4)] the uxon is attracted by the sem iuxon and, in the absence of a bias current, they \annihilate", resulting in a positive semi uxon ".

In Fig. 1 (a) one can see the  $\annihilation$  process of the sem i uxon situated at x = 3 and the uxon injected

at x = 6 (it corresponds to two lines at x 5 and x 7 at t = 0) for zero bias current = 0. If we trace the IVC of the state after annihilation, we get the curve shown in Fig. 2 by solid black symbols. As a horizontal axis we use the uxon velocity u normalized to the Swihart velocity and proportional to the voltage across the junction. In this notation a single uxon has an asymptotic velocity 1, two uxons have u! 2 as grows, etc.. At u = 0 the state of the system is the semi uxon "with maximum supercurrent (sem i uxon depinning current)  $0:63^{4,20,21,22}$ . W hen the bias current ex-" = 2= ceeds this value the system switches to the M cC um ber branch. By sweeping the bias current back one m ay trace the step with asymptotic velocity u = 3, corresponding to the state \*\*+#, which is form ed probably due to the topological instability of the solution sim ilar to the formation of zero- eld steps in conventional LJJ. The trajectories corresponding to the bias point d can be seen in Fig.1(d).

W hat happens if we inject a uxon while having a nonzero bias current? If the bias current as well as the distance between uxon injection point and sem i uxon are large enough, the uxon approaches the sem i uxon with rather high velocity and annihilation will not take place | the uxon will simply pass through the sem i uxon. Thus, injecting a uxon at a nite bias current we can trace an IVC which is shown in Fig. 2 by open symbols. The sem i uxon trajectories at the bias points b and c are shown in Fig. 1 (b) { (c), accordingly. O ne can see that in average a sem i uxon is shifted by the bias current away from the discontinuity point and oscillates around this new equilibrium position as the uxon bumps it. C om paring Fig. 1 (b) and (c), one can also notice that the

uxon's double line is more tight in (c) which is a result of relativistic contraction. Note that after the bias current is reduced to zero the annihilation takes place anyway and the system returns to the IVC corresponding to the state ", without a moving uxon, so that further sweeping of shows only the curve drawn by solid black symbols in Fig.2.

A ctually one can also trace the second uxon step with asymptotic velocity u = 2. It corresponds to the state \*+" and is shown in Fig. 2 by solid gray symbols. We were able to nd this state only starting from the point e at = 0.3 with a uxon situated at x = 5 and an anti uxon at x = 8. It is impossible to visualize this mode just by sweeping the bias current since this step is shadowed by ", \*\*+# and \*# steps.

## 2. Positive sem i uxon

Now we consider a semi uxon of a positive polarity initially present in the LJJ. The injected uxon and semi-

uxon repel each other and no annihilation can occur. Here we use the boundary conditions (4) with  $k_F = 1$ and  $k_{SF} = 1$  to obtain the IVC.By applying a smallbias current we push the uxon along the ring so it approaches

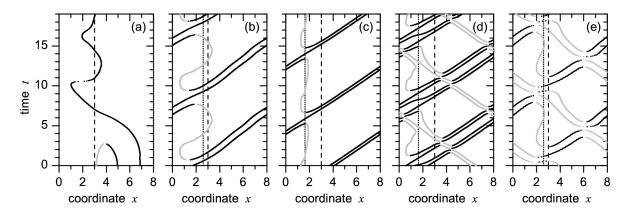


FIG.1: Trajectories of uxons (double line) and sem i uxons (single line) corresponding to annihilation \* + # = " at = 0 (a); dynamics in the state \* # at the rst uxon step at = 0.3 (b); at = 0.6 (c); dynamics at the third uxon step (state \* \* + ") at = 0.6 (d); dynamics at the second uxon step (state \* + ") at = 0.3. The vertical dashed line shows the position of the discontinuity. The vertical dotted line shows the position of the center of the static sem i uxon at the corresponding bias. In (a) for = 0 both lines coincide.

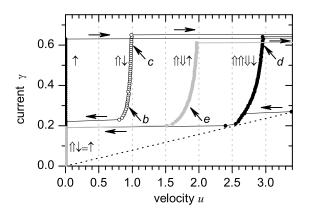


FIG.2: IVC after injection of a uxon into a 0- LJJ containing a semi uxon of negative polarity. The solid black symbols show the IVC after annihilation, open symbols show the IVC which can be traced if injection takes place at nite 2 = 2 + r = 0.21. Dotted line shows the position of the M cC umber branch (uniform phase-whirling state).

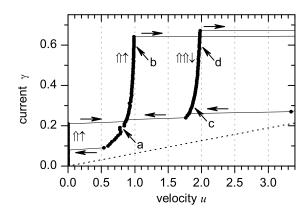


FIG. 3: Current voltage characteristic after injection of uxon into 0- -LJJ containing a sem i uxon of positive polarity. All (even and odd) uxon steps can be traced. The maximum supercurrent  $_{max}$  0.21. The trajectories at the bias points a{d are shown in Fig. 4 (a) { (d).

the semi uxon. For a small value of the bias current the situation is static as the driving force of the bias current can be compensated by the repulsion force between the uxon and the semi uxon. By increasing the bias current, the uxon moves closer to the sem i uxon and at som e critical value of the bias current overcom es the maximum possible repulsion force and passes through the sem i uxon. A fter this, the uxon keeps moving around the ring, bum ping the semi uxon once per cycle. The current voltage characteristic of this state is shown in Fig. 3. One can see that the maximum supercurrent  $c^{2} = \frac{2}{3}$ 0:21 (see Appendix A), corresponding to the maximum possible repulsion force between the uxon and the semi uxon, is considerably smaller than c = 2 = ofa single sem i uxon. Thus, the two situations can be distinguished.

The trajectories corresponding to the dynamics of the system are shown in Fig. 4 for several bias points marked in Fig. 3. We see that at the rst uxon step, see Fig. 4(b), the uxon (double line) moves progressively colliding with the semi uxon. The semi uxon corresponds to a more or less vertical line shifted to the right from the discontinuity point by the bias current. Note, that in Fig. 4 (a) we can see essentially the sam e dynam ics, but the sem i uxon is much more delocalized, probably because bias point a corresponds to the resonance which can be seen on the IVC in Fig. 3. We believe that this resonance may be related to the eigen-modes of the sem i uxon and to the Cherenkov emission of the plasm a waves which are excited when the uxon periodically bumps the semi uxon. The emitted plasm a wave form s a standing wave which interacts with a uxon and results in the resonance on the IVC.

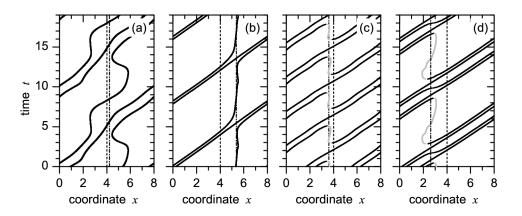


FIG. 4: Trajectories of sem i uxons in the state \*" (rst uxon step) for = 0.2 (a) and = 0.6 (b) and in the state \*\* # for = 0.3 (c) and = 0.6 (d). The vertical dashed line shows the position of the discontinuity. The vertical dotted line shows the position of the center of the static sem i uxon at the corresponding bias. In (a) for = 0 both lines coincide.

Thus, the polarity of the semi uxon can be probed by inserting a test uxon of known polarity and measuring the IVC. If a uxon and a semi uxon have the same polarity one should expect  $I_{m ax} = \frac{2}{3}$  0.21L and the appearance of the rst uxon step. If a uxon and a semi uxon have di erent polarities, one should expect  $I_{m ax} = \frac{2}{1c}$  0.63L and no rst uxon step provided the injection was made at = 0.

A nother di erence between these two con gurations is the value of the retrapping current r. As one can see from Figs. 2 and 3 the value of r in the \*# = " state is at least twice larger than for the \*" state.

A n interesting observation can be made, if we trace all uson branches of the IVC. In a usual annular LJJ with only one trapped uson (without a semi uson) one can observe uson steps at  $V = nV_1$  with only odd numbers n: the stone appears due to the motion of a single

uxon, the third one corresponds to an additional uxonanti uxon pair generated, the ffh one to two uxonanti uxon pairs, etc..

In an annular LJJ containing a uxon and a sem i uxon of the same polarity the situation is di erent. One can observe uxon steps with any integer n. This is especially easy to observe for the \*" state. The reason for this becomes clear after analysis of the trajectories shown in Fig. 4 for several bias points marked in Fig. 3.

W e see that at the second step, there are two positive uxons m oving in the sam e direction and the sem i uxon becam e of negative polarity \*\*#. This m eans that the sem i uxon ipped, and has em itted one positive uxon the process opposite to annihilation. Now, since there are two uxons which can m ove and one negative sem i-

uxon which cannot, the asymptotic voltage of the step is equal to  $2V_1$ . Still, the system can generate uxonanti uxon pairs which, together with semi uxon ipping, will result in uxon steps for all integer n.

A ctually, a similar e ect can be observed when initially the semi uxon had negative polarity. Then starting from the state " one could trace the uxon steps corresponding to the states \*#, \*+", \*\*+# (see Fig. 2). The trajectories for som e of the bias points can be seen in Fig. 1.

We also note that when the semi uxon polarity changes, the shift of the average position of the semiuxon changes too. This can be visualized using low temperature scanning electron microscopy<sup>23</sup>.

A nalyzing the trajectories while the bias point moves along the second uxon step we discovered that the two uxons are moving more or less equidistantly at a low value of the bias current, i.e., at the bottom of the step, as can be seen in Fig. 4 (c). When the bias current increases up to 0:45:::0:50 or above, the uxons bunch together as shown in Fig. 4 (d). The bunching appears because the plasm a waves, em itted during uxonsem i uxon collisions, result in an elective attracting potential between two uxons. We do not discuss this phe-

nom enon in detail here, but note that sim ilar bunching was observed in JJ arrays<sup>24</sup> or in stacks of LJJs<sup>25</sup>. In our case, the role of periodic obstacle is played by a sem iuxon. Generally speaking, the plasm a wave em ission

has a Cherenkov origin and is simply related to the peculiar dispersion relation for plasm a waves in the system under question<sup>26</sup>.

### B. Two sem i uxons in a ring

In the case of m ore than one sem i uxon of unknown polarity, the above read out procedure cannot give inform ation on the polarity of each of the sem i uxons, but allows to distinguish between states (a) "", (b) ##, and (c) "# or #". In other words, we can nd out the total ux hold by sem i uxons. Injecting the rst uxon in a sim ilar fashion as above, we measure the IVC. If the critical current is low, the uxon does not annihilate with sem i uxons and keeps moving around the ring. This can happen only if in the initial state both sem i uxons had the same polarity as the injected uxon. If, after injection of a uxon, I is still high, this means that the injected uxon has ipped one of the sem i uxons. In this case we inject a second uxon and so on. If I becomes lower after the rst injection, the initial state has been ""; if  $I_c$  becomes lower after second injection, the initial state has been "# or #"; and if  $I_c$  becomes lower after the third injection, the initial state has been ##.

### IV. CONCLUSIONS

We have shown that by introducing a test uxon of known polarity into the LJJ with a semi uxon of unknown polarity we can destructively read out the sem i-

uxon state. In principle, the read out can be made non-destructive, if after reading out the sem i uxon state we introduce another uxon of opposite polarity so that the system returns to its initial state (as before read out) as a result of uxon- uxon or uxon-sem i uxon annihilation. In case of two orm ore sem i uxons one can read out the total number of positive and negative sem i uxons. This technique is also applicable to arbitrary fractional

-vortices, but not very close to = 0 or = 2 where depinning currents for both N = 0 and N = 1 approach zero.

We have also investigated uxon steps in an annular LJJ with a -discontinuity. We found that one can trace the uxon steps corresponding to all integer n, instead of only odd n like in conventional LJJ with one trapped uxon. We have observed a smooth transition to the state of two bunched uxons in the \*\*# state.

Further, in appendix A we have derived the Eq. (A 9) which gives the depinning current of N uxons pinned by an arbitrary -vortex. We discovered that the biggest obstacle for a uxon is a fractional 1-vortex with 1 0.861 rather than a semi uxon. The formula  $\bigstar$  10) allows to compute the size N of the fractional vortex which is the biggest obstacle for N uxons trying to pass it.

### A cknow ledgm ents

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### APPENDIX A: DEPINNING OF FLUXONS BY AN ARBITRARY FRACTIONAL VORTEX

Since one can study experimentally arbitrary – vortices<sup>7</sup>, here we calculate the depinning current for a chain of N uxons that are pinned by and are trying to pass an arbitrary –vortex in a LJJ of in nite length.

The static version of Eq. (2) for arbitrary discontinuity is:

$$xx = \sin [ (x)] ; \qquad (A1)$$

where

$$for x < 0; \qquad for x < 0; \qquad for x > 0$$

W e write separately the Eqs. for the part of the junction to the left and to the right from discontinuity, situated at x = 0. After integration one arrives to the following two equations.

$$y_{1}() = x = 2 \frac{p}{2} \frac{1}{C_{1}()} \cos \frac{p}{c_{2}} (x < 0; (A 2a))$$

$$y_{2}() = x = 2 \frac{p}{2} \frac{1}{C_{2}()} \cos(\frac{p}{c_{2}}) (x < a) \frac{p}{c_{2}} (x < b)$$

A ssuming that

$$_{x}(1) = 0;$$
 (A3)

$$(1) = \arcsin;$$
 (A4)

$$(+1) = \arcsin + 2 N + ;$$
 (A5)

we arrive to the following expressions for  $C_1$  and  $C_2$ :

$$C_{1}() = \frac{p}{1} \frac{1}{2} + \arcsin ; \qquad (A 6)$$
  

$$C_{2}() = \frac{p}{1} \frac{1}{2} + \arcsin + (2 N + ); (A 7)$$

We use the phase plane analysis<sup>15</sup> to nd possible static con gurations. The trajectories on the phase plane  $y_{1,2}$  ( ) corresponding to Eqs. (A 2) are shown in Fig. 5 for = 0,  $< _{c}$  and =  $_{c}$ . At = 0 the uxon and fractional vortex are separated by a large distance. The uxon corresponds to the trajectory between point L (x = 1) and point M. The fractional vortex corresponds to the trajectory between point M and point R (x = +1) and contains a point P where the black and gray trajectories intersect, i.e., the phase crosses the 0- -boundary. From Fig. 5(a) { (c) one can see that with increasing the intersection point P shifts until, at the critical value of  $= _{c}$  the trajectories just touch each other at point P, as shown in Fig. 5(c). For larger, no intersection is possible and the static solution does not exist.

The critical value of at which the switching between trajectories is still possible is de ned by the following conditions:

$$y_1() = y_2(); y_1^0() = y_2^0();$$
 (A8)

This conditions are satis ed for  $=\frac{1}{2}(3 + )$ , which leads us to the nalresult:

$$_{c}() = \frac{2}{2 N +} \sin \frac{1}{2}$$
: (A 9)

The plot of this dependence for di erent N is shown in Fig. 6. The  $_{\rm c}$ () has reasonable limiting behavior (absence of pinning for N > 0) for ! 0 and ! 2 . For depinning of a uxon (N = 1) by a semi uxon,  $_{\rm c}$ () = 2=3 0.21. It is interesting that  $_{\rm c}$ () has a

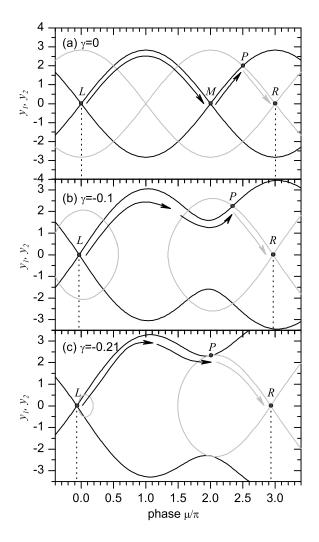


FIG. 5: The trajectories on the phase plane corresponding to Eqs. (A2). Black color corresponds to  $y_1$  (0-part), the gray color corresponds to  $y_2$  (-part). The trajectories are presented for a uxon pinned by a semi uxon (N = 1, = ) and (a) = 0, (b) = 0:1 and (c) = 0:21. A rrows are shown to guide the eye. A rrows show the path which corresponds to going from x = 1 (point L) to x = +1 (point R).

maximum not at = but a bit shifted, at  $_1=0.861$ , i.e., a  $_1$ -vortex is the biggest obstacle for a  $\,$  uxon. For two and three  $\,$  uxons the biggest obstacles are vortices with  $_2=0.918\,$  and  $_3=0.942\,$ . All  $_N$  can be found from the equation

$$\tan \frac{N}{2} = \frac{N}{2} + N$$
 : (A10)

Note, that in the lim it N ! 1 , N !

Our result (A 9) is also valid in the case N = 0 and gives the \depinning" current of the -vortex itself. The result (A 9) coincides with the expression obtained recently for the critical current of an annular junction in the presence of a -discontinuity of the phase (current dipole) created by injectors<sup>20</sup>. In fact one can even say that our result

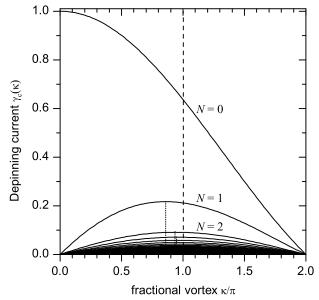


FIG.6: The dependence  $_{\rm c}$ () calculated for di erent N using Eq.(A9). The dashed line shows = corresponding to the sem i uxon. Three dotted lines show the values 1, 2 and 3 which correspond to the fractional vortices which cause the maximum possible pinning for N = 1;2;3 uxons.

(A 9) and the one of Ref. 20 are the same at least if one considers annular LJJ. In fact, if we denote  $^{0} = 2 N +$ , we can rewrite (A 9) as

$$_{\rm c}$$
 ( <sup>0</sup>) =  $\frac{2\sin\frac{1}{2}}{0}$ ; (A 11)

exactly as in Ref. 20. Physically this means that when one creates a large discontinuity  $^{0} = 2 \text{ N} + \text{ in an annu-}$ lar LJJ, it autom atically relaxes into N uxons trying to pass through the fractional -vortex under the action of bias current. The interesting result is that the Eq. (A 9) for an in nitely long linear junction and Eq. A 11) for an annular one coincide regardless of \ uxon crowding" which may take place in annular LJJ because of its nite length.

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- <sup>26</sup> E.Goldobin, A.W allra, and A.V.Ustinov, J.Low Temp. Phys. 119, 589 (2000).
- <sup>27</sup> W e note that such annular junctions cannot be constructed using natural 0 or junctions because one part cannot be simultaneously 0 and . There should be always an even number of 0- -joints. In an experiment the proposed situation can be realized using articial 0- -LJJ based on conventional superconductors with a pair of -injectors<sup>7</sup>. This case of only one discontinuity in a ring is very interesting as it allows to go beyond the possibilities o ered by nature.
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